Product Preview

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.60 \text{ V}$ at $I_F = 10 \text{ A}$

Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- These Devices are Pb-Free and Halogen Free/BFR Free

Typical Applications

- Switching Power Supplies including Telecom AC to DC Power Stages
- High Voltage DC-DC Converters
- Freewheeling and OR-ing Diodes
- Output Rectifier in Welding Power Supplies
- Industrial Automation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

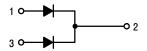


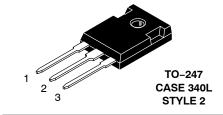
ON Semiconductor®

http://onsemi.com

VERY LOW FORWARD
VOLTAGE, LOW LEAKAGE
SCHOTTKY BARRIER
RECTIFIERS 60 AMPERES,
200 VOLTS

PIN CONNECTIONS





MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

G = Pb-Free Package

This document contains information on a product under development. ON Semiconductor reserves the right to change or discontinue this product without notice.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current (Rated V_R , T_C = 112°C) Per device (Rated V_R , T_C = 133°C) Per diode	I _{F(AV)}	60 30	Α
Peak Repetitive Forward Current (Rated V_R , Square Wave, 20 kHz, T_C = 115°C) Per device (Rated V_R , Square Wave, 20 kHz, T_C = 128°C) Per diode	I _{FRM}	120 60	Α
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	300	Α
Operating Junction Temperature	TJ	-55 to +150	°C
Storage Temperature	T _{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating		Value	Unit
Typical Thermal Resistance Junction-to-Case Per Diode Junction-to-Case Per Device	$R_{ heta JC}$	0.72 0.63	°C/W
Junction-to-Ambient Per Diode Junction-to-Ambient Per Device	$R_{ hetaJA}$	40.62 40.17	

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage (Note 1)	V _F			V
$(I_F = 10 \text{ A}, T_J = 25^{\circ}\text{C})$ $(I_F = 15 \text{ A}, T_J = 25^{\circ}\text{C})$		0.74 0.79	-	
(I _F = 15 A, I _J = 25 °C) (I _F = 30 A, T _J = 25 °C)		1.04	1.90	
$(I_F = 10 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 15 \text{ A}, T_J = 125^{\circ}\text{C})$ $(I_F = 30\text{A}, T_J = 125^{\circ}\text{C})$		0.60 0.64 0.74	- - 0.85	
Instantaneous Reverse Current (Note 1) $(V_R = 180 \text{ V}, T_J = 25^{\circ}\text{C})$ (Rated dc Voltage, $T_J = 25^{\circ}\text{C})$	I _R	3 5	- 100	μ Α μ Α
$(V_R = 180 \text{ V}, T_J = 125^{\circ}\text{C})$ (Rated dc Voltage, $T_J = 125^{\circ}\text{C}$)		5.3 7	- 30	mA mA

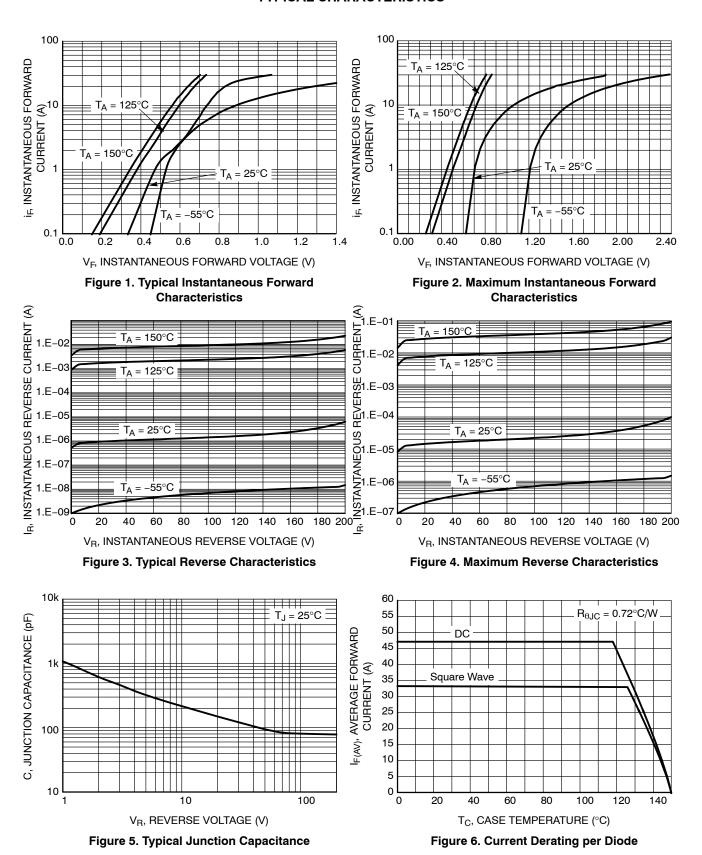
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Package	Shipping
NTSW60200CTG	TO-220AB (Pb-Free, Halide Free)	30 Units / Rail

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

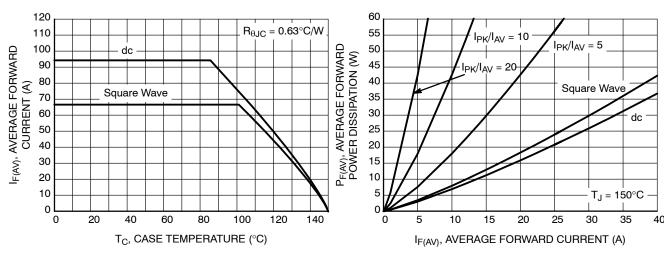


Figure 7. Current Derating per Device

Figure 8. Forward Power Dissipation

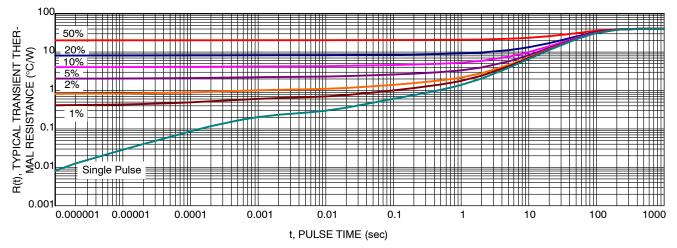
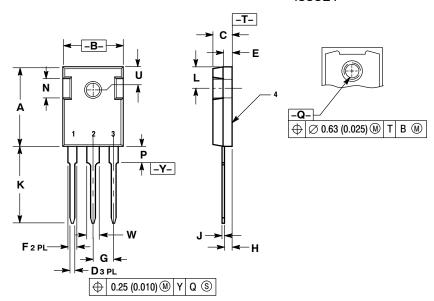


Figure 9. Typical Transient Thermal Response

PACKAGE DIMENSIONS

TO-247 CASE 340L-02 ISSUE F



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 5M 1982
- 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	20.32	21.08	0.800	8.30
В	15.75	16.26	0.620	0.640
С	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
Е	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
Н	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
Р		4.50		0.177
Ø	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

STYLE 2:

- PIN 1. ANODE
 - 2. CATHODE (S)
 - B. ANODE 2 4. CATHODES (S)

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